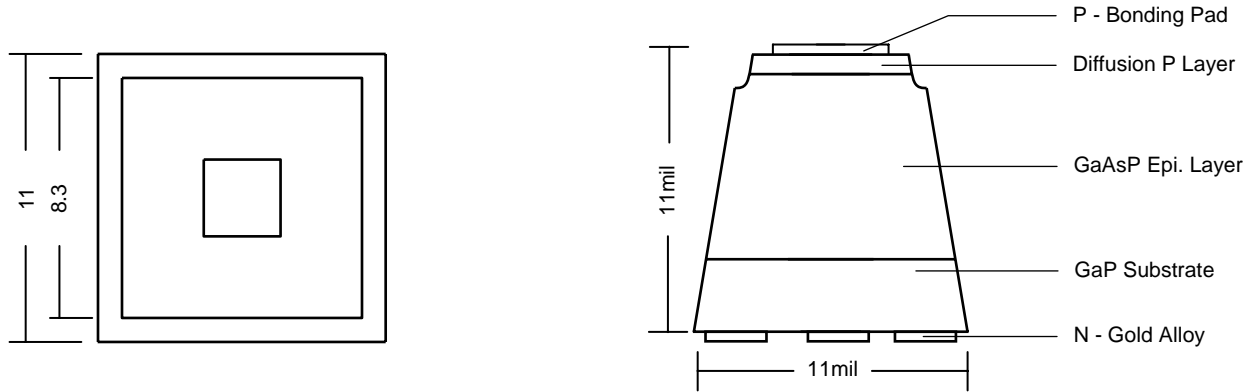


TCT11HY

GaAsP



❖ Outline Dimensions:



❖ Physical Structure:

Chip dimensions		Chip size	11 mil x 11 mil	280 μm x 280 μm
		Thickness	11 mil	280 μm
		Emission area	8.3 mil	210 μm
Electrode	Top	P (anode)	Aluminium (Gold optional)	
	Backside	N (cathode)	Gold alloy	
Surface condition		Not frosted		

❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$	-	2.10	2.50	V
Reverse Current	I_R	$V_R = 5\text{V}$	-	-	10	μA
Wavelength	λ_P	$I_F = 20\text{mA}$	-	583	-	nm
	Hue	$I_F = 20\text{mA}$	-	585	-	
Spectral Width at Half Height	$\Delta\lambda$	$I_F = 20\text{mA}$	-	32	-	nm
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Luminous Intensity	I_V	$I_F = 20\text{mA}$	3.5	4.5	-	mcd